Market News

OptiMOS™ Linear FET combines a low $R_{DS(on)}$ with a large Safe Operating Area

Munich, Germany – 25 July 2017 – Infineon Technologies AG (FSE: IFX / OTCQX: IFNNY) launches the OptiMOS™ Linear FET series. This new product family combines the state-of-the-art on-state resistance ($R_{DS(on)}$) of a trench MOSFET with the wide Safe Operating Area of a planar MOSFET. This solves the trade-off between $R_{DS(on)}$ and linear mode capability. The OptiMOS Linear FET can operate in the saturation region of an enhanced mode MOSFET. It is the perfect fit for hot-swap, e-fuse, and protection applications commonly found in telecom and battery management systems (BMS).

Both, the rugged linear mode operation and the higher pulse current contribute to low conduction losses, faster start-up, and shorter down time. The OptiMOS Linear FET prevents damage at the load if there is a short circuit, by limiting high in-rush currents.

Availability

The OptiMOS Linear FET is available now in three voltage classes: 100 V, 150 V, and 200 V. They can be supplied in either a D^2PAK or D^2PAK 7pin package. These industry standard packages offer a compatible footprint for drop-in replacement. More information is available at www.infineon.com/optimos-linearfet.

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